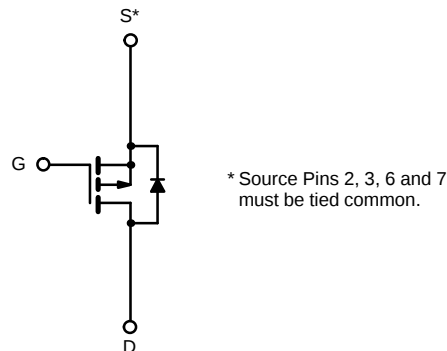
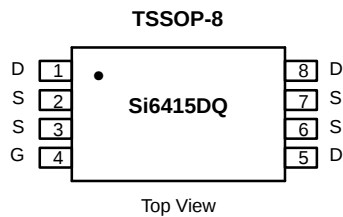




P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-30	0.019 @ $V_{GS} = -10$ V	± 6.5
	0.030 @ $V_{GS} = -4.5$ V	± 5.2

TrenchFET®
Power MOSFETs



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	$T_A = 25^\circ\text{C}$	I_D	± 6.5	A
	$T_A = 70^\circ\text{C}$		± 5.2	
Pulsed Drain Current		I_{DM}	± 30	
Continuous Source Current (Diode Conduction) ^a		I_S	-1.5	
Maximum Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	1.5	W
	$T_A = 70^\circ\text{C}$		1.0	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	83	$^\circ\text{C/W}$

Notes

a. Surface Mounted on FR4 Board, $t \leq 10$ sec.

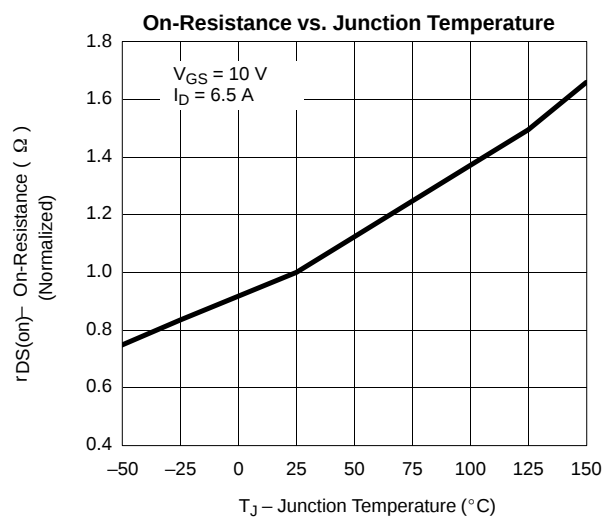
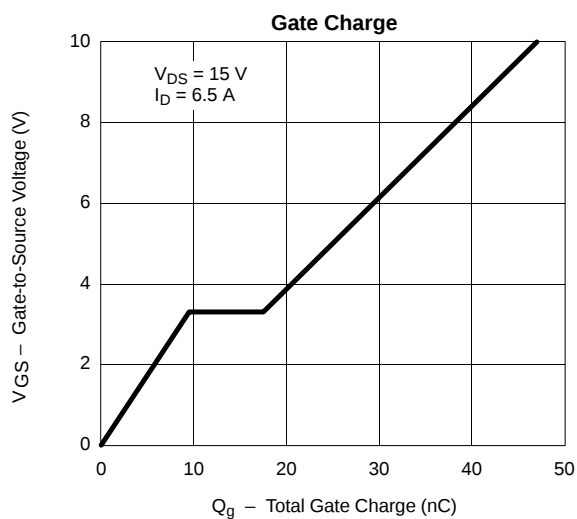
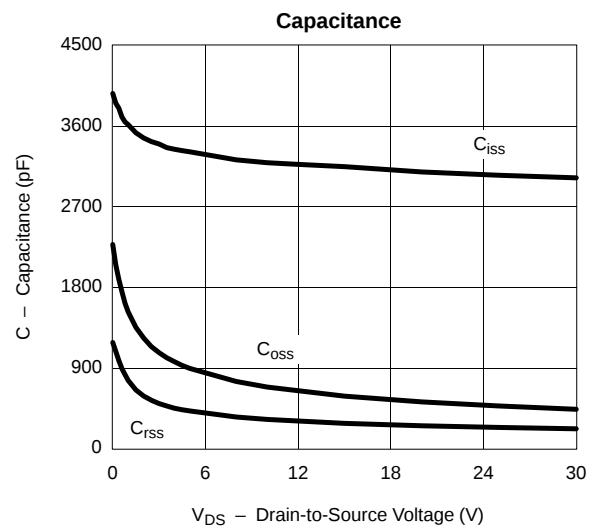
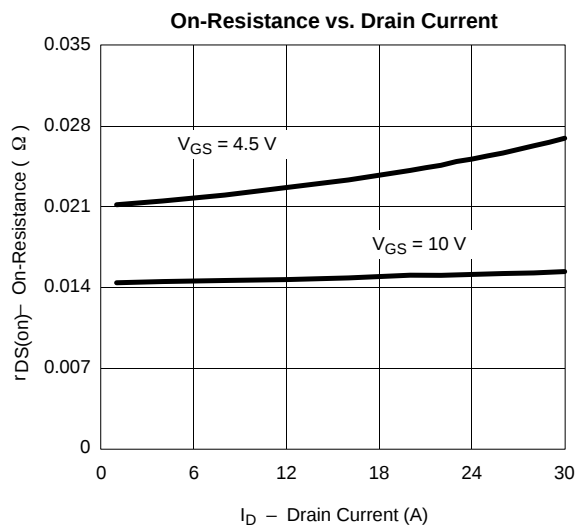
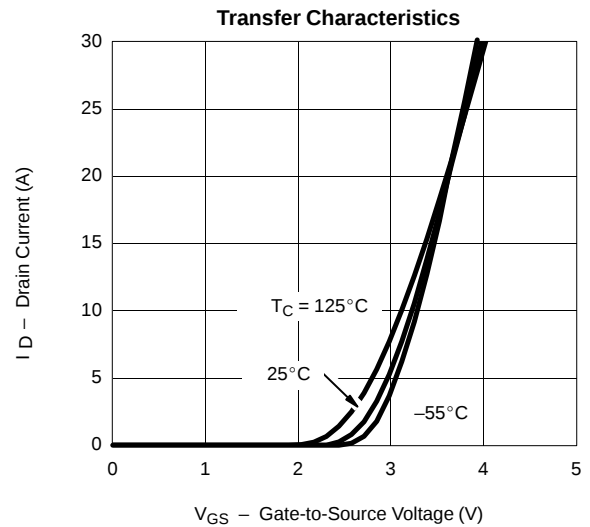
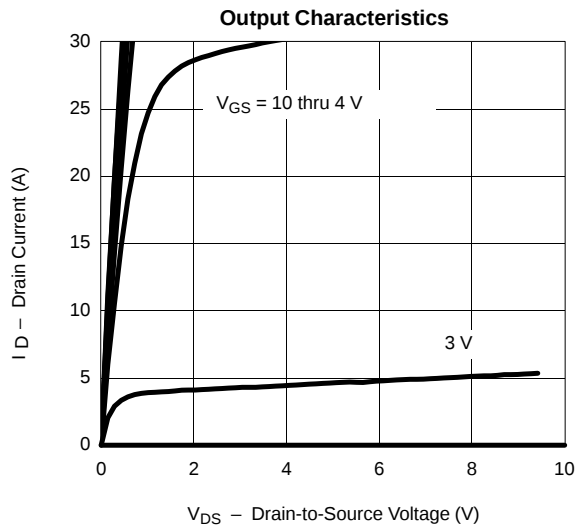
SPECIFICATIONS (T_J = 25° C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-1.0			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -30 V, V _{GS} = 0 V, T _J = 55°C			-25	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -10 V	-20			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -10 V, I _D = -6.5 A		0.015	0.019	Ω
		V _{GS} = -4.5 V, I _D = -5.2 A		0.022	0.030	
Forward Transconductance ^a	g _{fs}	V _{DS} = -15 V, I _D = -6.5 A		18.5		S
Diode Forward Voltage ^a	V _{SD}	I _S = -1.5 A, V _{GS} = 0 V		-0.75	-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -15 V, V _{GS} = -10 V, I _D = -6.5 A		47	70	nC
Gate-Source Charge	Q _{gs}			9.5		
Gate-Drain Charge	Q _{gd}			8		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -15 V, R _L = 15 Ω I _D ≈ -1 A, V _{GEN} = -10 V, R _G = 6 Ω		16	30	ns
Rise Time	t _r			17	30	
Turn-Off Delay Time	t _{d(off)}			73	110	
Fall Time	t _f			31	60	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = -1.5 A, di/dt = 100 A/μs		40	60	

Notes

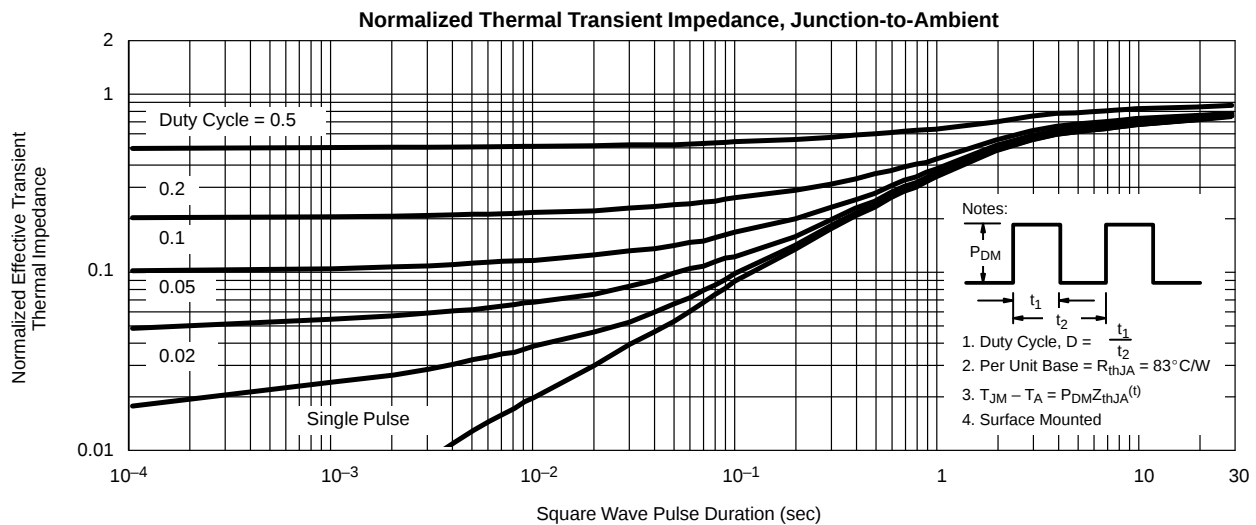
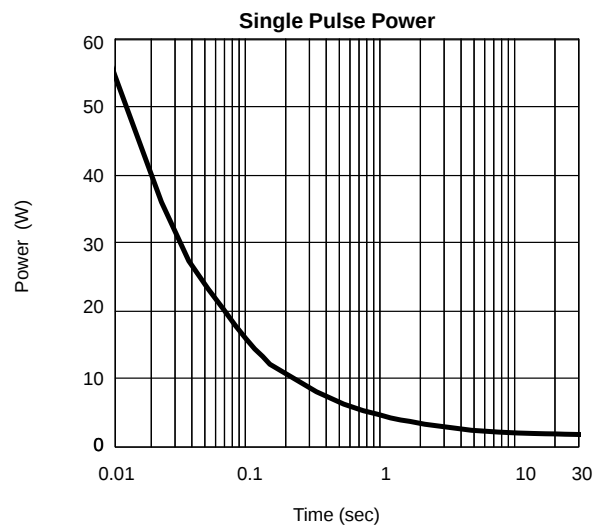
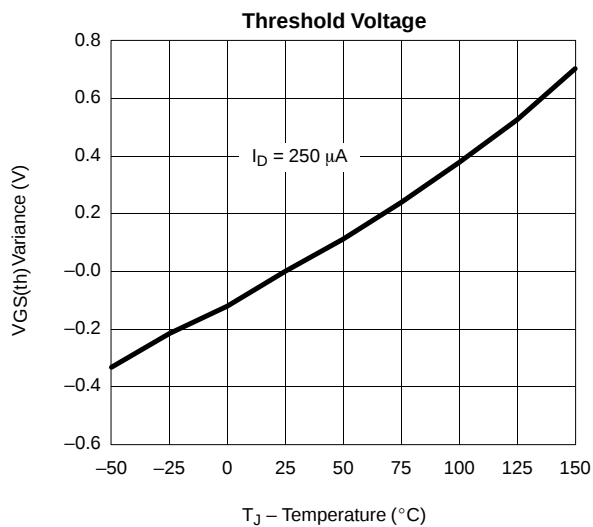
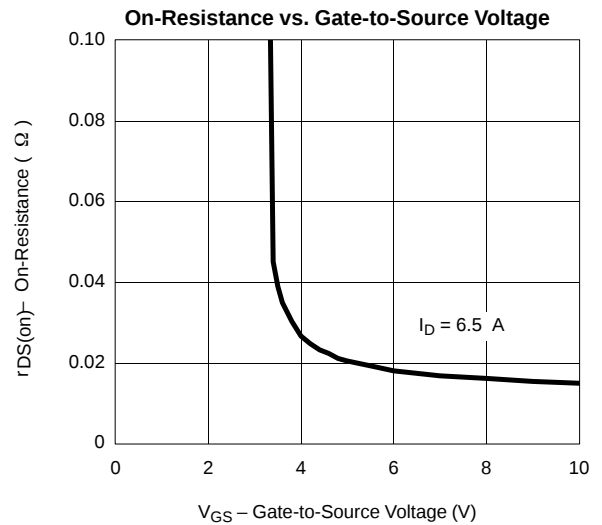
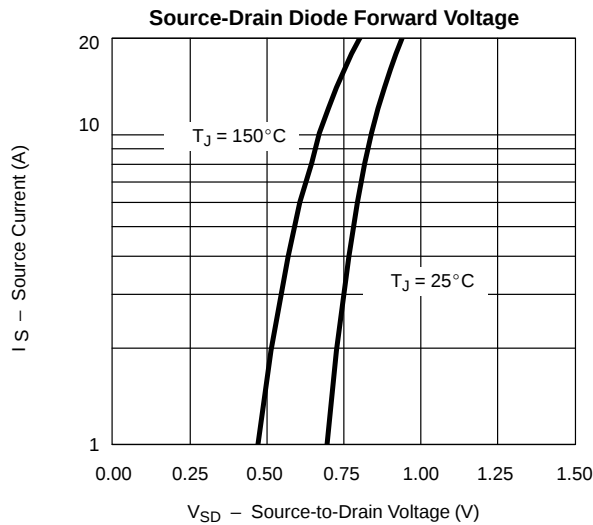
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





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